

Form PTO-1449 (MODIFIED)	U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE	ATTY. DOCKET NO. 032026-0754	SERIAL NO. 10/772,573
		APPLICANT Luke J. Mawst, et al.	
		FILING DATE 02/05/2004	GROUP ART UNIT 2811

INFORMATION DISCLOSURE CITATION

(Use several sheets if necessary)

U.S. PATENT DOCUMENTS

EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUB-CLASS	FILING DATE IF APPROPRIATE
<i>A.L.</i>		5,793,787	8/11/98	Meyer, et al.			
<i>A.L.</i>		2004-0061102	4/1/04	Tansu			
<i>A.L.</i>		5,383,211	1/95	Van de Walle, et al.			
<i>A.L.</i>		6,621,842	9/03	Dapkus			

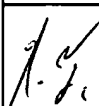

FOREIGN PATENT DOCUMENTS


	REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUB-CLASS	TRANSLATION	
							YES	NO
<i>A.L.</i>		WO 01/29943	4/26/01	PCT				

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<i>A.L.</i>	H. C. Casey, Jr., "Temperature dependence of threshold current density on InP-Ga _{0.28} In _{0.72} As _{0.6} P _{0.4} (1.3 μm) double heterostructure lasers," J. Appl. Phys., Vol. 56 (7), 1984, pp. 1959-1964.
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<i>A.L.</i>	M. Kondow, T. Kitatani, S. Nakatsuka, M. C. Larson, K. Nakahara, Y. Yazawa, M. Okai, and K. Uomi, "GaInNAs : A novel material for long wavelength semiconductor lasers," IEEE J. Select. Topic Quantum Electronic., Vol. 3, 1997, pp. 719-730.
<i>A.L.</i>	A. F. Phillips, A. F. Sweeney, A. R. Adams, and P. J. A. Thijs, "Temperature Dependence of 1.3- and 1.5-μm Compressively Strained InGaAs(P) MQW Semiconductor Lasers," IEEE. J. Select. Topics Quantum Electron., Vol. 5, No. 3, May/June 1999, pp. 401-412.
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EXAMINER	DATE CONSIDERED
<i>[Signature]</i>	9/18/05
<p>* EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include any copy of this form with next communication to applicant.</p>	

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OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)							
		I. Vurgaftman and J.R. Meyer, "(In) GaAsN-based type-II 'W' quantum-well lasers for emission at $\lambda=1.55\mu\text{m}$," Appl. Phys. Lett., Vol. 83, No. 14, 6 October 2003, pp. 2742-2744.					
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